

**Amendments to the Brief Description of the Drawings:**

Please Amend the Specification as follows:

(Currently Amended) ~~FIG.~~ FIGS. 1A through 1C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to an embodiment of the present invention.

(Currently Amended) ~~FIG.~~ FIGS. 2A through 2C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the embodiment of the present invention.

(Original) FIG. 3 is a graph showing the relation between mixture ratio and etching selectivity for an etching gas used in the process step of forming a multilayer interconnect according to the embodiment of the present invention, and the relation between the composition of a fluorocarbon gas used as an element of the etching gas and the etching selectivity.

(Original) FIG. 4 is a cross-sectional view illustrating a checking interconnect for checking a multilayer interconnect formed in the method for forming a multilayer interconnect of the embodiment.

(Original) FIGS. 5A through 5C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to a first known example.

(Currently Amended) FIGS. 6A ~~through 6C~~ and 6B cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the first known example.

(Currently Amended) FIGS. 7A ~~through 7C~~ and 7B are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the first known

example.

(Currently Amended) FIGS. **8A** through ~~**8C**~~ and **8B** are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to a second known example.